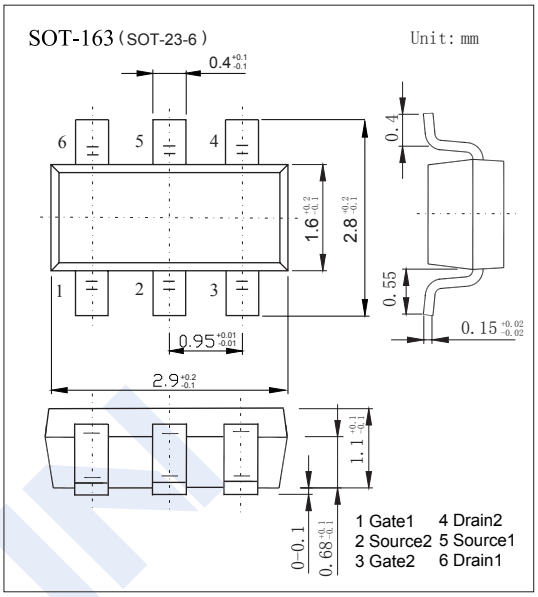
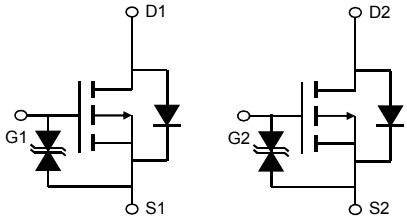
Dual P-Channel MOSFET

AO6801E (KO6801E)



■ Features

- V_{DS} (V) =-30V
- I_D =-2A (V_{GS} =-10V)
- $R_{DS(ON)}$ < 110mΩ (V_{GS} =-10V)
- $R_{DS(ON)}$ < 135mΩ (V_{GS} =-4.5V)
- $R_{DS(ON)}$ < 185mΩ (V_{GS} =-2.5V)
- ESD Rating: 2000V HBM



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±12	
Continuous Drain Current	T_A=25°C	I_D	-2	A
	T_A=70°C		-1.6	
Pulsed Drain Current		I_{DM}	-15	
Power Dissipation	T_A=25°C	P_D	0.7	W
	T_A=70°C		0.45	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R_{thJA}	180	℃/W
	Steady-State		230	
Thermal Resistance.Junction- to-Lead		R_{thJL}	180	
Junction Temperature		T_J	150	℃
Junction Storage Temperature Range		T_{stg}	-55 to 150	

Dual P-Channel MOSFET

AO6801E (KO6801E)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=-250μA, V_{GS}=0V	-30			V
Gate-Source breakdown voltage	BV_{GSO}	V_{DS}=0V, I_G=±250uA	±12			
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V, V_{GS}=0V			-1	uA
		V_{DS}=-30V, V_{GS}=0V, T_J=55℃			-5	
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±12V			±10	uA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.7		-1.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-2A			110	mΩ
		V_{GS}=-10V, I_D=-2A T_J=125℃			158	
		V_{GS}=-4.5V, I_D=-1.5A			135	
		V_{GS}=-2.5V, I_D=-1A			185	
On state drain current	$I_{D(ON)}$	V_{GS}=-10V, V_{DS}=-5V	-15			A
Forward Transconductance	g_{FS}	V_{DS}=-5V, I_D=-2A		7		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-15V, f=1MHz		305		pF
Output Capacitance	C_{oss}			42		
Reverse Transfer Capacitance	C_{rss}			26		
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz		8.5	17	Ω
Total Gate Charge (10V)	Q_g	V_{GS}=-10V, V_{DS}=-15V, I_D=-2A		7	12	nC
Total Gate Charge (4.5V)				3.5	6	
Gate Source Charge	Q_{gs}			0.7		
Gate Drain Charge	Q_{gd}			1.2		
Turn-On DelayTime	$t_{d(on)}$	V_{GS}=-10V, V_{DS}=-15V, R_L=7.5Ω, R_{GEN}=3Ω		6		ns
Turn-On Rise Time	t_r			4		
Turn-Off DelayTime	$t_{d(off)}$			23		
Turn-Off Fall Time	t_f			7		
Body Diode Reverse Recovery Time	t_{rr}	I_F=-2A, dI/dt=500A/μs		9.5		
Body Diode Reverse Recovery Charge	Q_{rr}			13.5		nC
Maximum Body-Diode Continuous Current	I_S				-1	A
Diode Forward Voltage	V_{SD}	I_S=-1A,V_{GS}=0V			-1	V

* The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	V1**

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AO6801E (KO6801E)

■ Typical Characterisitics

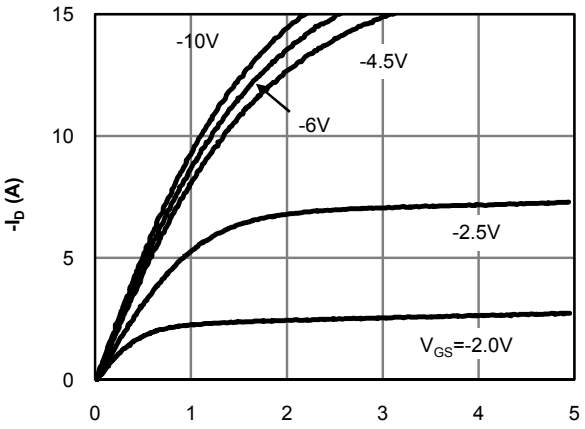

Fig 1: On-Region Characteristics (Note E)

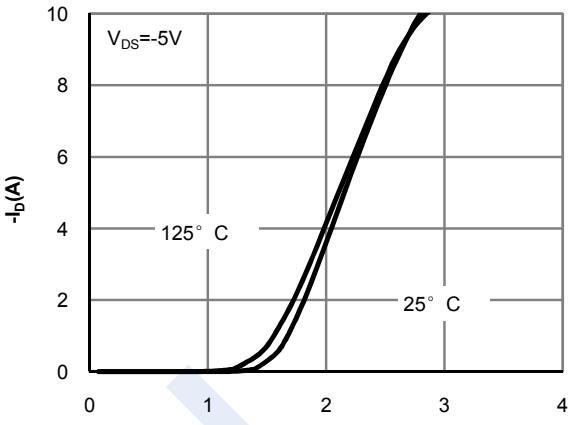

Figure 2: Transfer Characteristics (Note E)

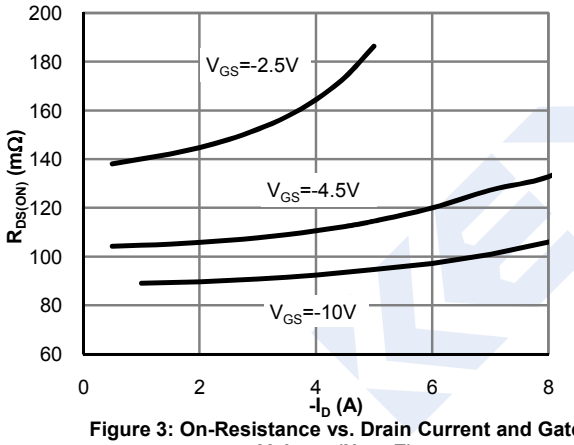

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

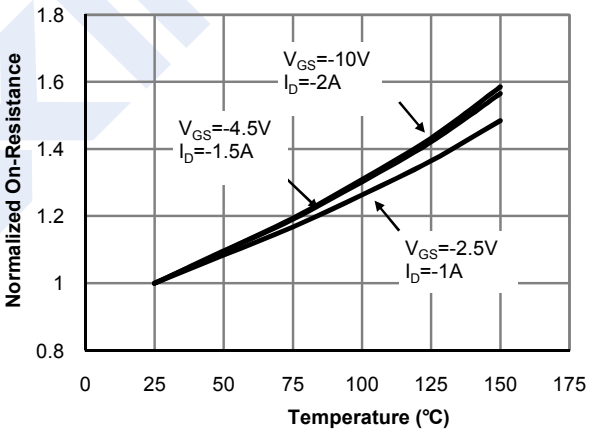

Figure 4: On-Resistance vs. Junction Temperature (Note E)

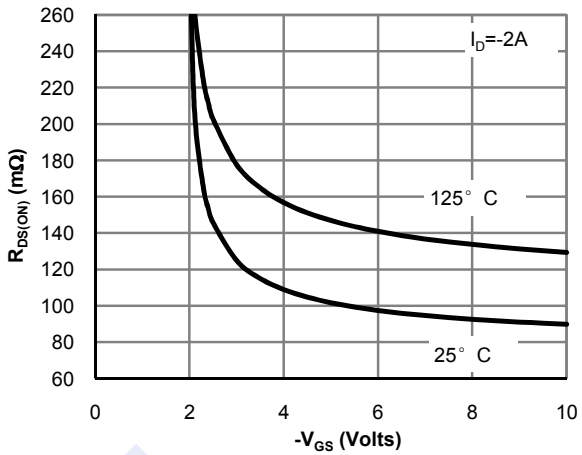

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

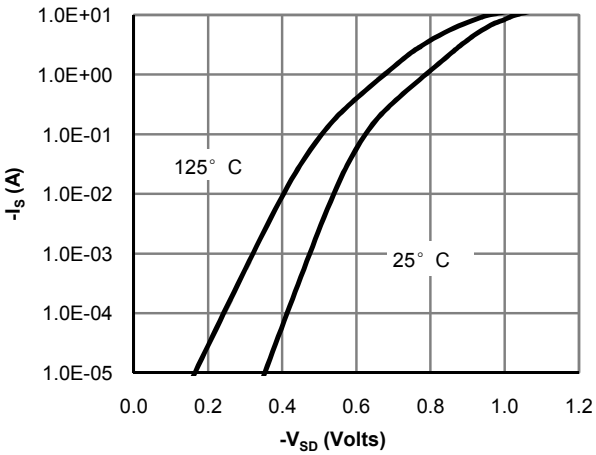

Figure 6: Body-Diode Characteristics (Note E)

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■ Typical Characterisitics

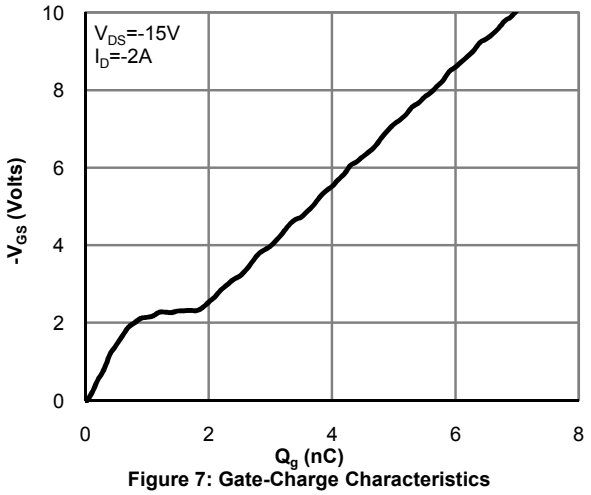


Figure 7: Gate-Charge Characteristics

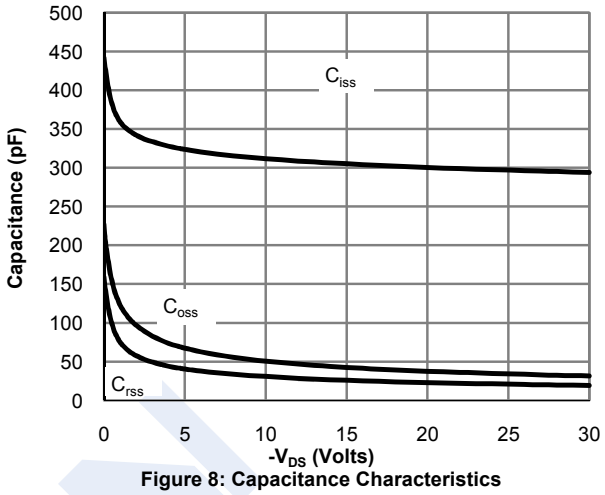


Figure 8: Capacitance Characteristics

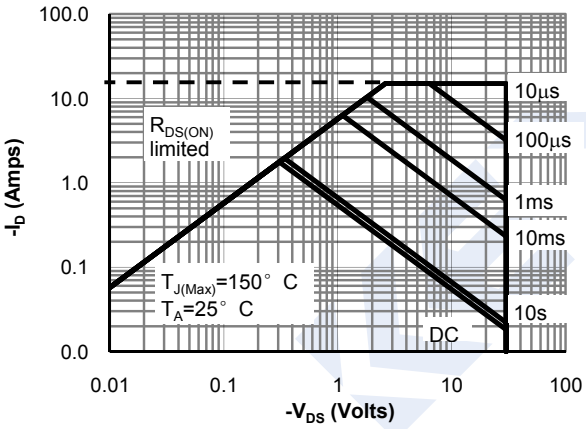
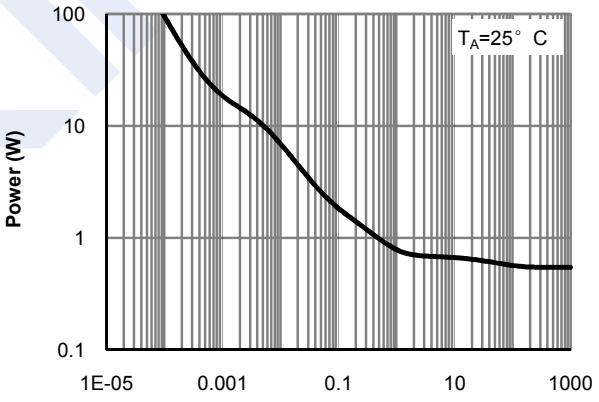


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)



Pulse Width (s)

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

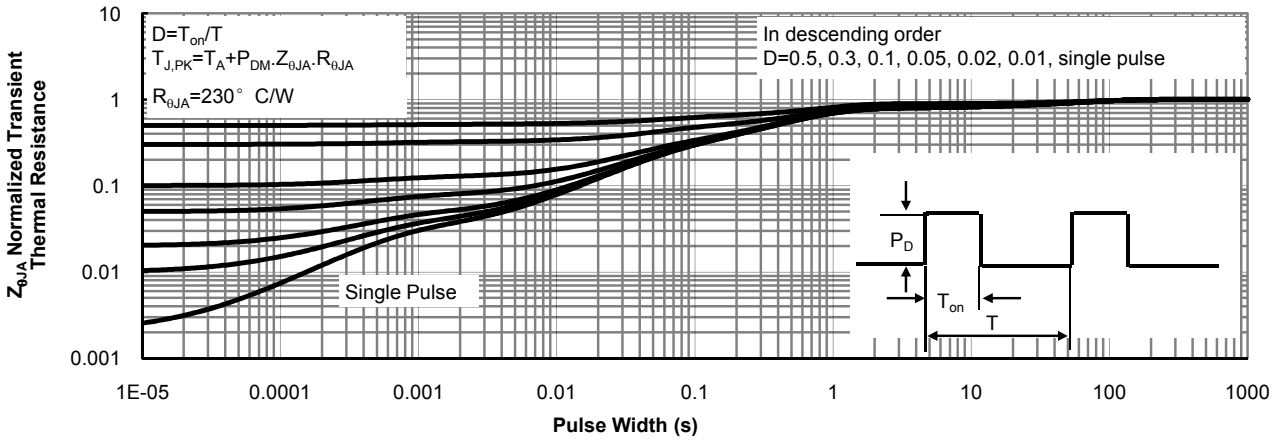


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)